100V Half-Bridge GaN Driver with Dual PWM Inputs

1. Features

- Independent High-Side & Low-Side Logic Inputs
- Split Outputs for Adjustable Turn-on/-off Speeds
- Strong 1-Ω Pull-Up and 0.2-Ω Pull-Down Resistance
- Internal Strong and Smart Bootstrap Switch
- Fast Propagation Delay (14ns Typical)
- Excellent Delay Matching (1ns Typical)
- High-Side Floating Supply Operates up to 100V DC
- Built-In UVLO, OVLO, OTP Protections
- 35μA Low VCC Quiescent Current
- WLCSP 1.62mmx1.62mm Package

2. Applications

- Half-Bridge and Full-Bridge Converters
- High-Voltage Synchronous DC-DC Converters
- High Frequency, High Power Density Applications
- 48V DC Motor Drive
- High Power Class-D Audio Power Amplifier
- Automotive 48V/12V Bi-directional DC-DC

3. Description

The INS2001 is a 100V half-bridge driver designed to efficiently drive both high-side and low-side gallium nitride (GaN) field effect transistor (FET). Specifically designed for GaN FETs, the INS2001 solves numerous challenges traditionally faced with conventional MOSFET driver solutions. An internal smart bootstrap (BST) switch prevents overcharging of the high-side floating supply BST capacitor during dead times, thus protecting the gate of the GaN FET while maintaining consistent gate voltage for both sides of GaN FETs. Rich fault protection is provided including independent VCC and BST undervoltage lockout, VCC overvoltage lockout, and over temperature protection.

The INS2001 has two logic inputs to control high-side and low-side drivers independently for maximum flexibility, and drivers have split outputs to adjust turn-on and turn-off speeds separately. The strong driving capability and excellent delay matching make the INS2001 suitable for high power and high frequency applications.

4. Typical Application

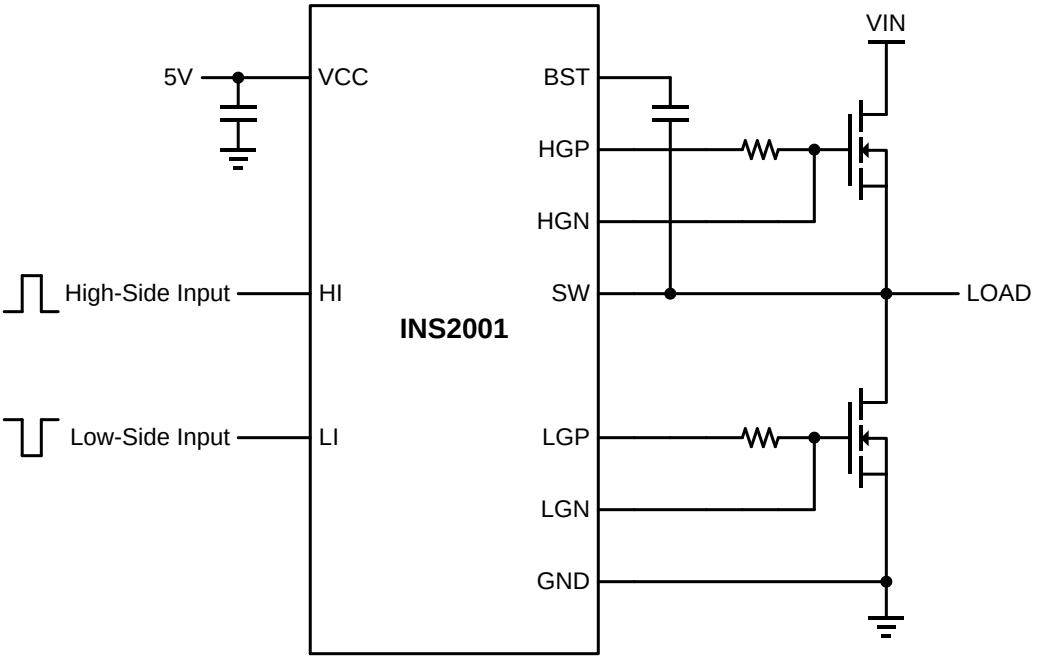


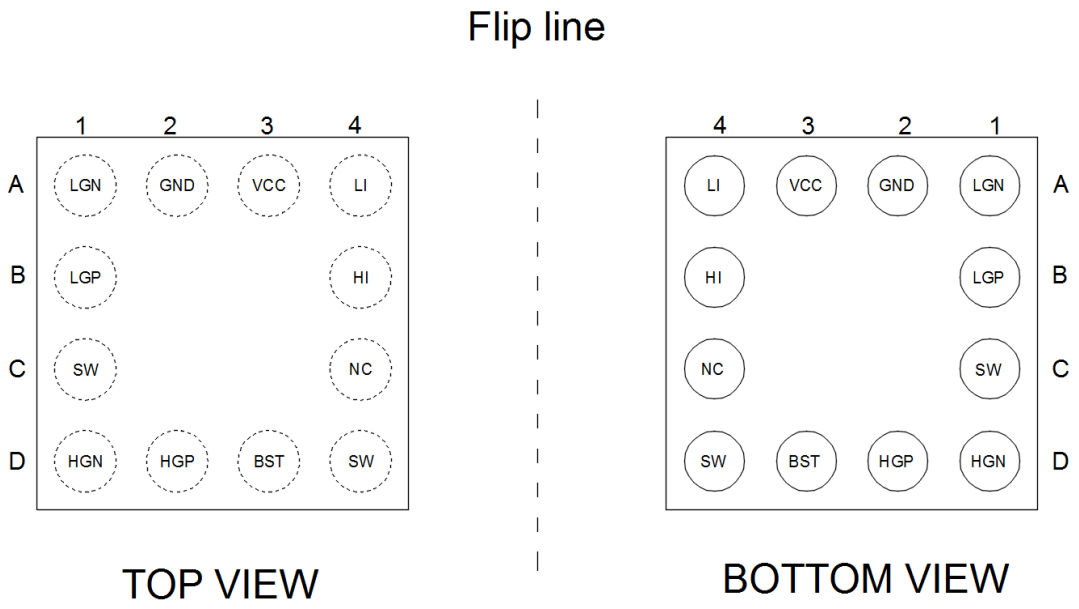
Table of contents

5. Revision History

Major changes since the last revision

Revision	Date	Description of changes
1.0	2024-05-15	Final datasheet release

6. Pin Configuration and Functions



12-Lead WLCSP (1.62mm x 1.62mm) Package

Pin Number	Pin Name	Description
A1	LGN	Low-Side Gate Driver Pull-Down Output. Connect to the gate of the low-side GaN FET. Use a resistor to adjust the turn-off speed.
B1	LGP	Low-Side Gate Driver Pull-Up Output. Connect to the gate of the low-side GaN FET. Use a resistor to adjust the turn-on speed.
C1, D4	SW	Switch Node. Connect to the negative terminal of the bootstrap capacitor, the source of the high-side GaN FET, and the drain of the low-side GaN FET.
D1	HGN	High-Side Gate Driver Pull-Down Output. Connect to the gate of the high-side GaN FET. Use a resistor to adjust the turn-off speed.
D2	HGP	High-Side Gate Driver Pull-Up Output. Connect to the gate of the high-side GaN FET. Use a resistor to adjust the turn-on speed.
D3	BST	High-Side Gate Driver Bootstrap Supply. Locally bypass this pin to SW with a ceramic bootstrap capacitor.
C4	NC	No Function Connection. This pin can be left open, connected to VCC or GND.
B4	HI	High-Side Gate Driver Control Input. This pin has an internal 200kΩ pull-down resistor.
A4	LI	Low-Side Gate Driver Control Input. This pin has an internal 200kΩ pull-down resistor.
A3	VCC	IC and Low-Side Gate Driver Supply. Locally bypass this pin to GND with a ceramic capacitor.
A2	GND	Ground. All signals are referenced to this ground.

7. Absolute Maximum Ratings

All pins are referred to GND, unless otherwise specified. Stress beyond the absolute maximum ratings can cause permanent damage or deteriorate device reliability and lifetime.

Parameter	Min	Max	Unit
VCC	-0.3	6	V
BST to SW	-0.3	6	V
HI, LI, NC	-0.3	6	V
HGP, HGN	SW-0.3	BST+0.3	V
LGP, LGN	-0.3	VCC+0.3	V
SW	-5	100	V
BST	-0.3	105	V
Operating Junction Temperature T_J	-40	150	˚C
Storage Temperature	-55	150	˚C

8. ESD Ratings

Parameter	Value	Unit
Human Body Model (HBM)	±2000	V
Charged Device Model (CDM)	±1000	V

9. Recommended Operating Conditions

Parameter	Min	Max	Unit
VCC	4.5	5.5	V
HI, LI	0	5.5	V
SW	-4	80	V
BST	SW+4.5	SW+5.5	V
SW Slew Rate		50	V/ns
Operating Junction Temperature T_J	-40	125	˚C

10. Thermal Information

Symbol	Parameter	INS2001W	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	76.34	˚C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case (Top)	4.19	˚C/W
$R_{\theta JB}$	Thermal Resistance, Junction to Board	21.95	˚C/W

11. Electrical Characteristics

T_J = 25°C, VCC = BST = 5V, SW = GND = 0V, HGP = HGN, LGP = LGN, unless otherwise noted.

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Supply Input						
VCC Quiescent Current	I_{CC-Q}		35	60	μA	HI = LI = 0V
VCC Operating Current	I_{CC-OP}		1	2	mA	f = 500kHz
BST Quiescent Current	I_{BST-Q}		40	70	μA	HI = LI = 0V
BST Operating Current	I_{BST-OP}		1	2	mA	f = 500kHz
VCC Overvoltage Rising Threshold	V_{CC-OVR}	5.7	6	6.3	V	
VCC Overvoltage Hysteresis	$V_{CC-OVHYS}$		0.25		V	
VCC Undervoltage Rising Threshold	V_{CC-UVR}	3.9	4.1	4.3	V	
VCC Undervoltage Hysteresis	$V_{CC-UVHYS}$		0.3		V	
BST Undervoltage Rising Threshold	$V_{BST-UVR}$		3.6		V	
BST Undervoltage Hysteresis	$V_{BST-UVHYS}$		0.5		V	
PWM Input						
Input High Threshold	V_{IH}		1.8	2.2	V	
Input Low Threshold	V_{IL}	0.8	1.2		V	
Input Hysteresis	V_{I-HYS}		0.6		V	
Input Pull-Down Resistance	R_I		200		kΩ	
Bootstrap Switch						
Low-Current Forward Voltage			0.02	0.2	V	$I_{VCC-BST}$ = 100μA
High-Current Forward Voltage			0.4		V	$I_{VCC-BST}$ = 100mA
Switch On Resistance	$R_{BST(ON)}$		4		Ω	
High-Side and Low-Side Gate Driver						
Output Pull-Down Resistance	R_{DN}		0.2	1	Ω	I_{HGN} or I_{LGN} = 100mA
Output Pull-Up Resistance	R_{UP}		1	2	Ω	I_{HGP} or I_{LGP} = -100mA
Output Peak Source Current (1)	I_{OH}		1.7		A	HG = SW or LG = GND
Output Peak Sink Current (1)	I_{OL}		4.3		A	HG = BST or LG = VCC
Over Temperature Protection						
OTP Shutdown Rising Threshold(1)	T_{OTP}		165		°C	
OTP Shutdown Hysteresis(1)	$T_{OTP-HYS}$		20		°C	

12. Switching Characteristics

T_J = 25°C, VCC = BST = 5V, SW = GND = 0V, HGP = HGN, LGP = LGN, unless otherwise noted.

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Minimum Input Pulse Width that Changes the Output (1)	T_{IPW}		5		ns	
Minimum Gate Output Pulse Width (1)	T_{OPW}		12		ns	
Gate Output Rise Time (1)	T_R		7		ns	C_L = 1nF, 10% to 90%
Gate Output Fall Time (1)	T_F		3		ns	C_L = 1nF, 90% to 10%
High-Side Turn-Off Propagation Delay (1)	T_{HPHL}		14		ns	HI falling to HG falling
High-Side Turn-On Propagation Delay (1)	T_{HPLH}		14		ns	HI rising to HG rising
Low-Side Turn-Off Propagation Delay (1)	T_{LPHL}		14		ns	LI falling to LG falling
Low-Side Turn-On Propagation Delay (1)	T_{LPLH}		14		ns	LI rising to LG rising
Delay Matching LG On and HG Off (1)	T_{MON}		1	5	ns	
Delay Matching LG Off and HG On (1)	T_{MOFF}		1	5	ns	

(1) Not 100% tested and guaranteed by design.

13. Typical Characteristics

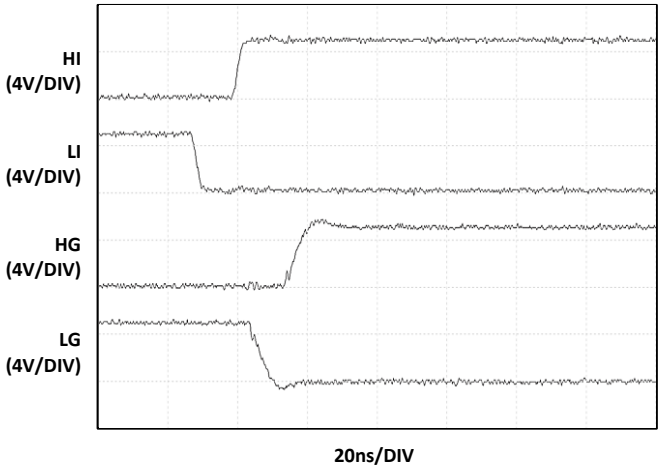


Figure 1. HG Turn-On and LG Turn-Off Waveform, C_{OUT} = 1nF

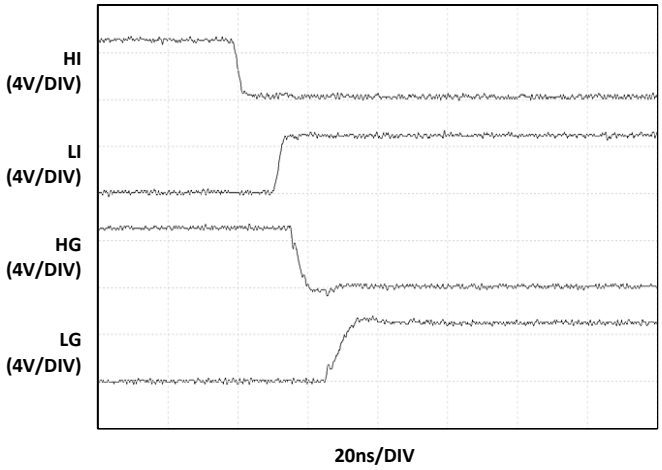


Figure 2. HG Turn-Off and LG Turn-On Waveform, C_{OUT} = 1nF

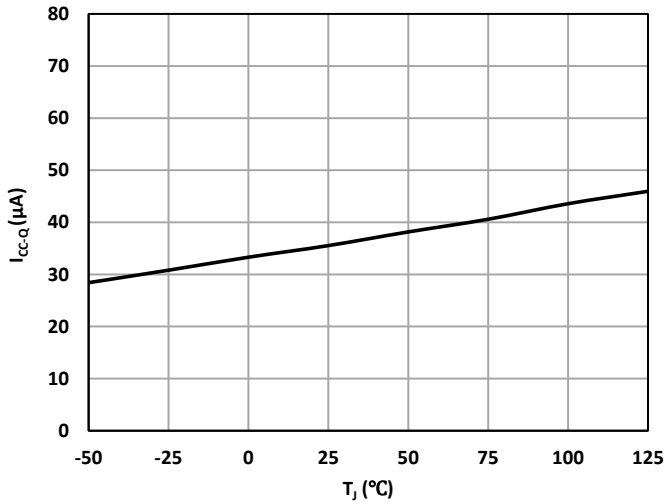


Figure 3. VCC Quiescent Current vs Temperature

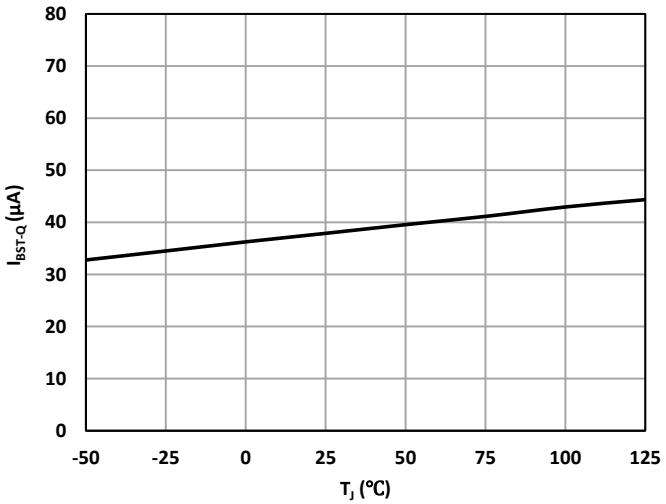


Figure 4. BST Quiescent Current vs Temperature

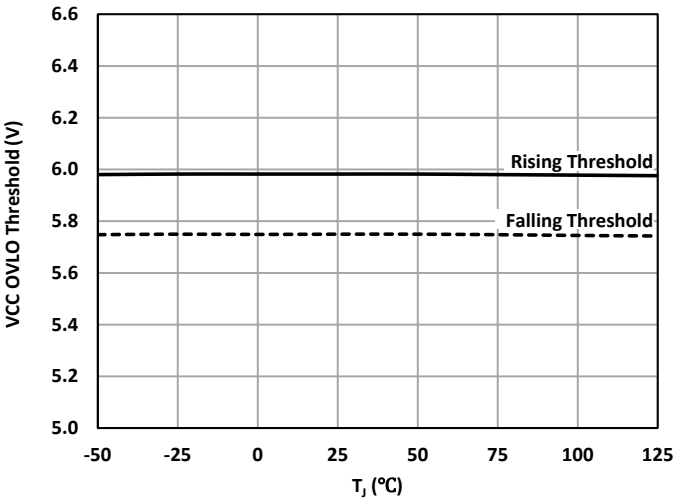


Figure 5. VCC OVLO Threshold vs Temperature

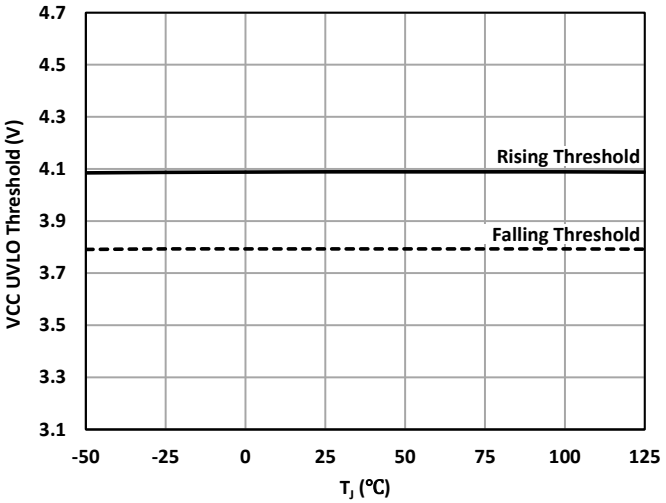


Figure 6. VCC UVLO Threshold vs Temperature

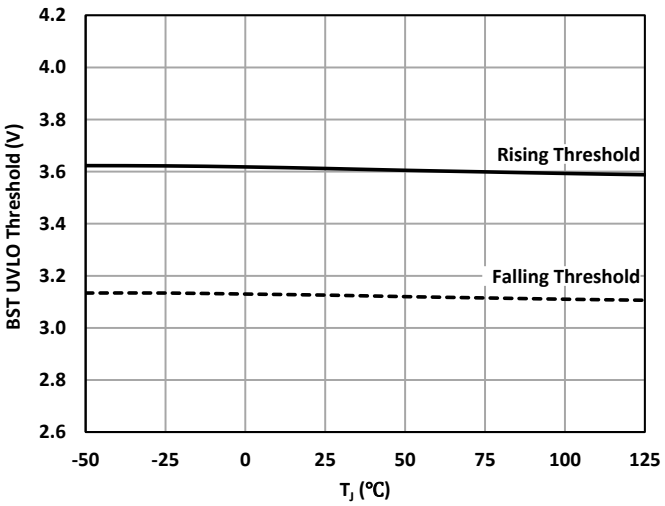


Figure 7. BST UVLO Threshold vs Temperature

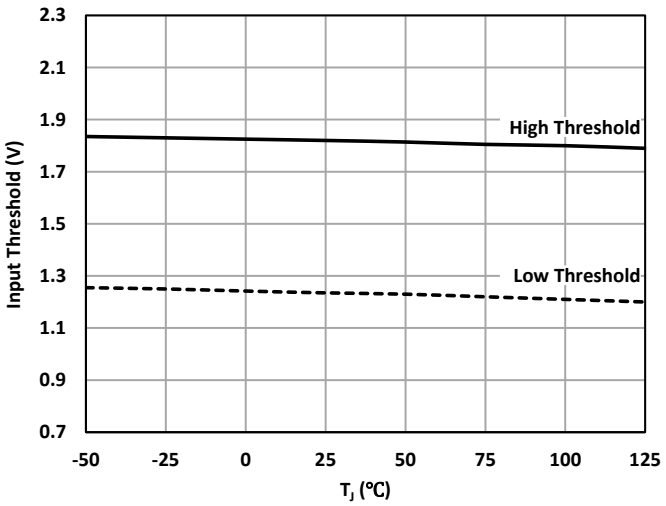


Figure 8. PWM Input Threshold vs Temperature

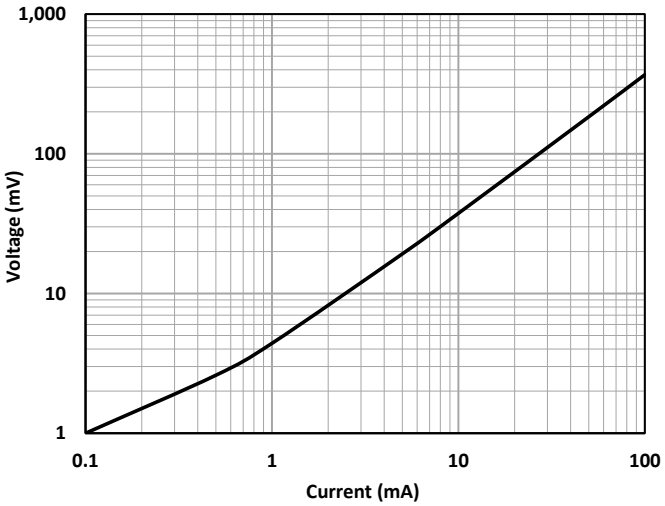


Figure 9. Bootstrap Forward Voltage vs Current

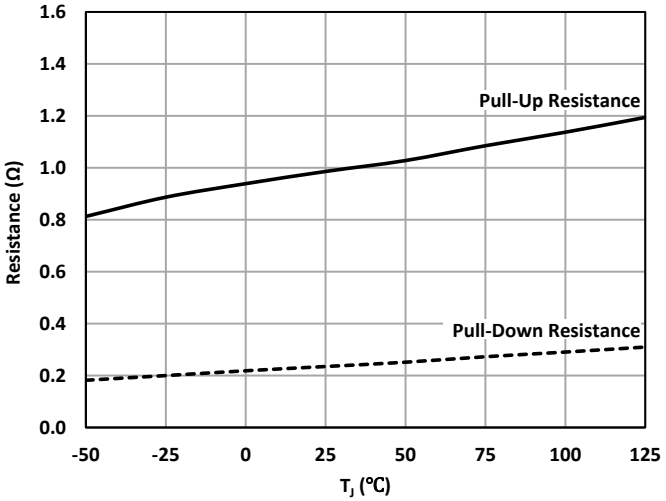


Figure 10. Output Pull-Down/Pull-Up Resistance vs Temperature

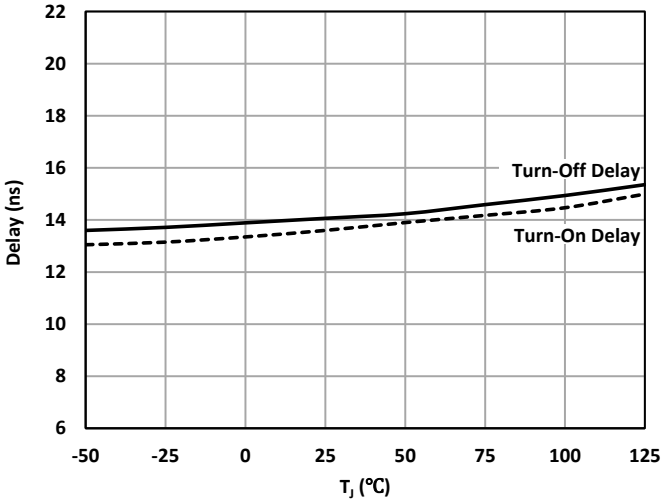


Figure 11. Low-Side Propagation Delay vs Temperature

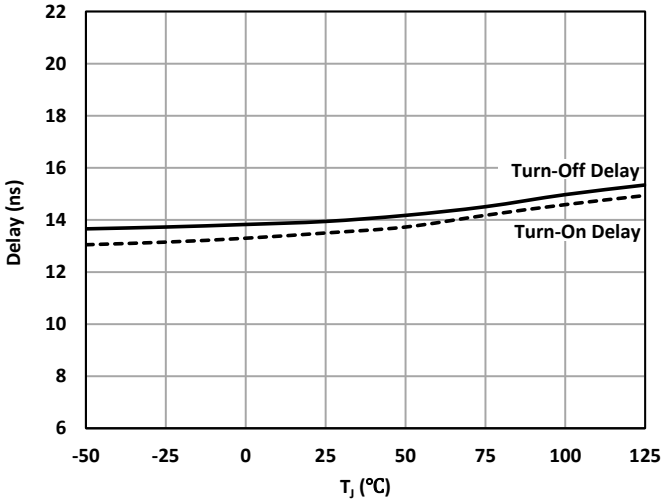


Figure 12. High-Side Propagation Delay vs Temperature

14. Block Diagram

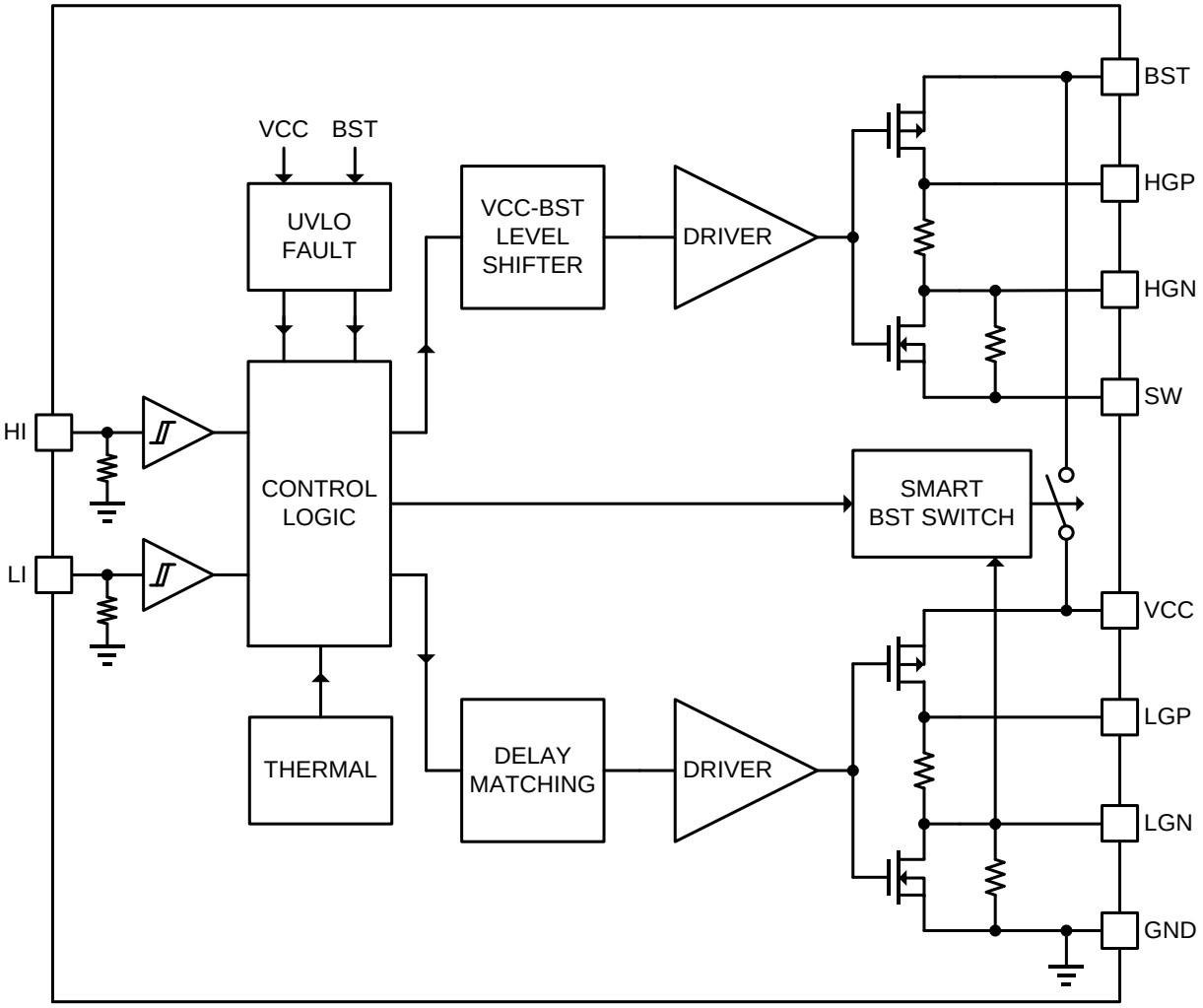


Figure 13. Functional Block Diagram

15. Function Description

The INS2001 is a 100V half-bridge driver optimized for GaN FETs, designed to address the specific challenges encountered when driving GaN FETs with traditional MOSFET drivers. It incorporates an integrated smart BST switch to manage the high-side floating supply so that it charges the BST capacitor to match the VCC supply when the low-side driver turns on. This ensures a consistent gate voltage for both high-side and low-side GaN FETs, preventing overcharging and potential damage to their gates while also ensuring precise delay matching, an important factor for accurately controlling switching dead times.

The INS2001 also provides split gate driver outputs, enabling the independent adjustment of turn-on and turn-off slew rates for both high-side and low-side drivers by connecting different gate resistors. With its strong driving capability and excellent delay matching, the INS2001 is highly suitable for supporting multiple topologies, including buck, boost, buck-boost, and a variety of high-power and high-frequency applications.

Input and Output

The INS2001 input pins, HI and LI, are independent and TTL logic compatible with the ability to withstand input voltages up to 5.5V regardless of VCC voltage. Table 1 shows the truth table of input and output. The INS2001 offers fast propagation delay (14ns typical) with excellent delay matching (1ns typical) between the high-side and low-side driver channels, making it ideal for high-frequency applications. Both inputs feature a 5ns (typical) input deglitch filter to remove any unwanted pulses from a PWM input. A narrow input pulse exceeding this deglitch delay time will be extended to a minimum output pulse of 12ns (typical) to ensure proper gate turn-on and turn-off transients. Figure 14 shows the switching characteristics of the input and output. The INS2001 allows HG and LG to overlap for turn-on; however, a carefully managed non-overlapping dead-time, $T_{DTH/DTL}$, is recommended for the input interface to avoid a possible shoot-through condition. Both input pins, HI and LI, have an internal pull-down resistor of 200kΩ.

Table 1. Input and Output Truth Table

HI	LI	HGP	HGN	LGP	LGN
L	L	Open	L	Open	L
L	H	Open	L	H	Open
H	L	H	Open	Open	L
H	H	H	Open	H	Open

Note: When an output is “Open”, it is connected to another split output through the internal 10kΩ resistor.

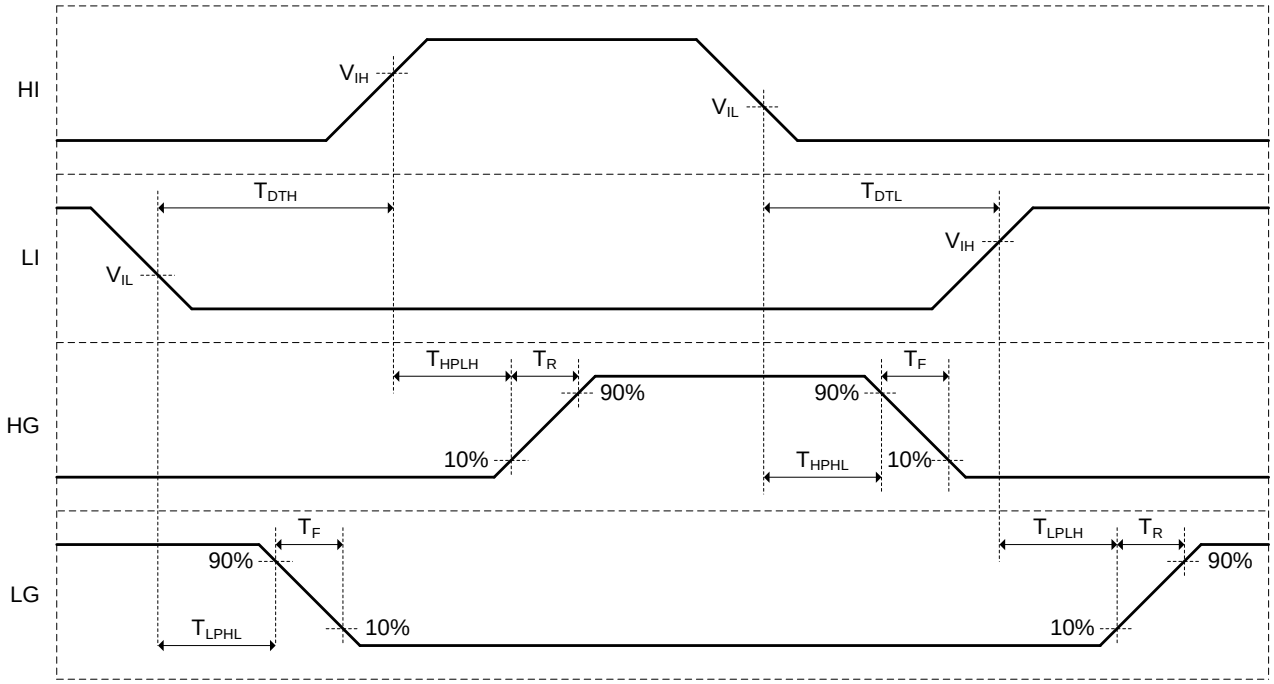


Figure 14. Timing Diagram of Input and Output

Split Gate Driving Output

The INS2001 provides split gate driver outputs for both high-side and low-side GaN FETs, offering flexibility to adjust both turn-on and turn-off strengths independently. This is achieved by connecting additional gate resistors at HGP, HGN, LGP, and LGN pins, targeting optimization of efficiency, reliability, and EMI performance. The strong pull-down and pull-up gate strength of the INS2001 are optimized for driving GaN FETs, enabling high-frequency and high-efficiency operations. With a strong pull-down strength of 0.2Ω (typical) at HGN and LGN pins, it provides a robust low impedance path necessary for eliminating high dv/dt induced gate turn-on. Meanwhile, the pull-up strength of 1Ω (typical) at HGP and LGP pins helps in reducing the switching spikes and overshoot voltages at the switch node. HGN and LGN pins have internal 50kΩ pull-down resistors to SW node and GND nodes, respectively, and are also internally connected to HGP and LGP via 10kΩ resistors, respectively.

VCC UVLO/OVLO Protections

The INS2001 features undervoltage lockout (UVLO) and overvoltage lockout (OVLO) for VCC, providing the operation under the safe conditions of devices. When the VCC voltage falls below its UVLO threshold of 3.8V (typical) or exceeds above its OVLO threshold of 6.0V (typical), the INS2001 turns off both the high-side and low-side drivers and ignores the HI and LI inputs.

High dv/dt Rate GaN FET Switching

GaN FETs can switch much faster than traditional silicon based MOSFETs, requiring gate drivers capable of delivering precise and fast switching signals to fully leverage their potential. Managing high dv/dt rates during switching is important for stable gate driver circuitry, ensuring reliable and efficient operation. The INS2001 features an advanced level-shifting technology circuit designed to overcome these challenges associated with driving GaN FETs. Its advanced noise rejection mechanism ensures precise and accurate signal transmission between the control logic to driver outputs even in extreme high dv/dt environments up to 50V/ns.

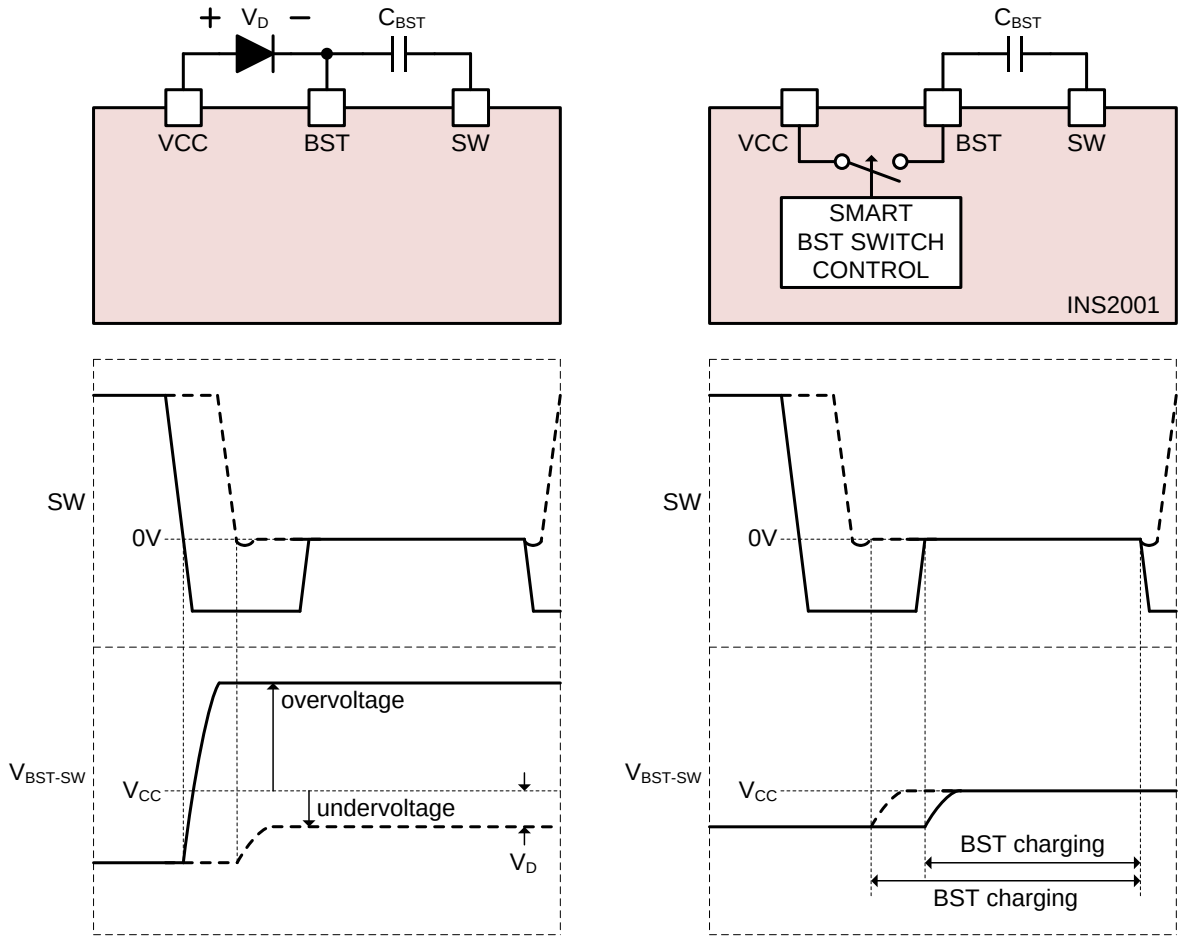
Another challenge in driving GaN FETs is the issue of high reverse conduction voltage. When the SW node drops below 0V due to this reverse conduction, it can temporarily lower the level shifter's supply rail, causing a disruption in the level shifter's output signals. This disruption can appear as a delay mismatch between signals transmitted to each side of the driver, resulting in timing inaccuracies and potential performance degradation. The advanced level shifter in the INS2001 is designed to prevent such conditions, ensuring that delay variation is kept to minimum (1ns typical) even when the SW node fluctuates down to -4V. Furthermore, the INS2001 features an additional delay matching circuit that parallels the proposed level shifter circuit, matching its process and temperature variation characteristic. This additional feature further improves delay matching to 1ns (typical).

High-Side Gate-Driver Supply

Despite GaN devices offering advantages with their superior figure of merit ($Q_G \times R_{DSON}$) compared to silicon based MOSFET counterparts, their sensitivity to gate driving voltage levels presents a challenging concern. GaN devices are more vulnerable to both overvoltage and undervoltage conditions at the gate, which can have negative effects on their reliability and performance. The concern over gate overvoltage is more significant for GaN FETs, given that they are considerably more fragile compared to their silicon counterparts. Conversely, Insufficient gate voltage, or gate undervoltage, can result in increased switching losses and reduced efficiency.

To mitigate these challenges, the INS2001 features a smart BST switch that allows precise control for BST charging and blocking. Figure 15 illustrates the operation principle of the smart BST switch. Unlike silicon MOSFETs, GaN FETs typically lack an intrinsic body diode, resulting in higher reverse conduction voltages, (typically 2V to 3V or even higher at high current) during dead time. This can lead to overcharging of the BST capacitor, potentially causing permanent damage to the gate of the high-side GaN FET. In the INS2001, the BST switch's turning on and off are precisely controlled so that it allows charging of the BST capacitor only during SW node is fully reached at GND voltage when the low-side GaN FET is being turned on. Moreover, the BST switch exhibits a low on-impedance of 4Ω (typical), ensuring minimal dropout voltage. Accordingly, the INS2001 always maintains a well-balanced BST rail voltage close to VCC, achieving excellent delay matching and balanced gate driving strength between the high-side and low-side drivers.

Additionally, the INS2001 provides a BST UVLO protection with a falling threshold of 3.1V (typical) and a rising threshold of 3.6V (typical). When BST-SW falls below BST UVLO threshold, the INS2001 enters BST UVLO mode, turns off the high-side driver, but the low-side driver remains activated.



(a) Conventional Bootstrap Diode (b) Smart Bootstrap Switch

Figure 15. Operation Principle of Bootstrap Supply

Over Temperature Protection (OTP)

The INS2001 employs over temperature protection (OTP). If the internal junction temperature, T_j, exceeds 165°C (typical), The HI and LI inputs are ignored, and both the high-side and low-side drivers are turned off. When the temperature drops below 145°C (typical), the ISN2001 will resume normal operation.

Layout Recommendation

A proper PCB layout is essential to support high-power and high-frequency operation with GaN FETs. The PCB layout requires proper bypassing on (VCC-GND) and (BST-SW) and careful trace routing to minimize the parasitic of the gate driving and power loops. Check the following guidelines and Figure 16 to obtain the optimum performance from the INS2001.

1. Mount the bypass capacitors for (VCC-GND) and (BST-SW) as close as possible to the INS2001 package. Also place the bypass capacitors on the same side as the INS2001. Carefully implement the power loop to minimize the length of the copper trace.

2. Place the INS2001 as close as possible to the GaN FETs and keep the copper trace between the INS2001 and GaN FETs short and wide.

3. To minimize the gate voltage ringing, it is desirable to place gate resistors close to both the INS2001 and GaN FETs.

4. Place both high-side and low-side GaN FETs close together to minimize the parasitic inductance in between.

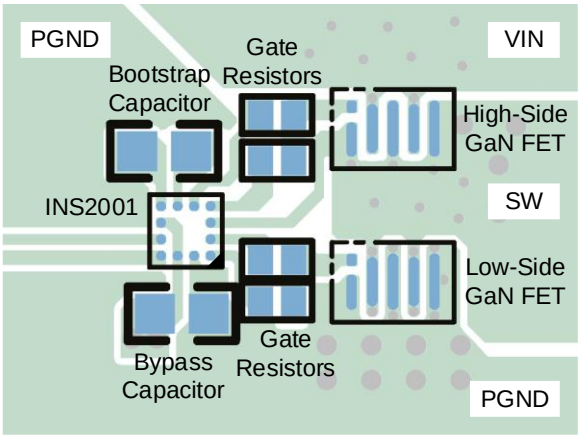
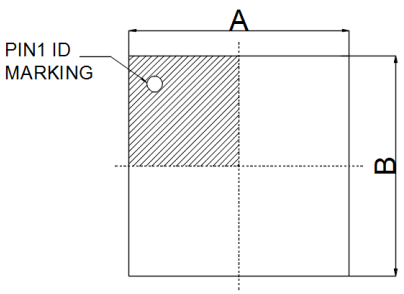


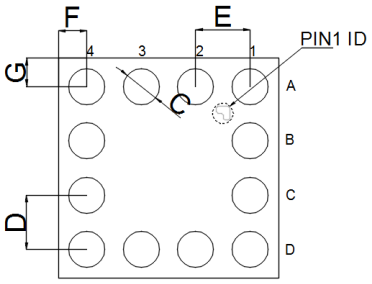
Figure 16. Layout Example

16. Package Information

WLCSP1.62X1.62-12L Package:

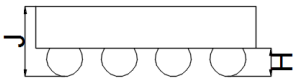


TOP VIEW



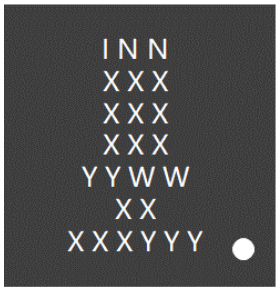
BOTTOM VIEW

SYMBOL	MILLIMETER			NOTE
	MIN	NOM	MAX	
A	1.595	1.620	1.645	
B	1.595	1.620	1.645	
C	0.236	0.262	0.288	12X
D		0.40 BASIC		6X
E		0.40 BASIC		6X
F		0.21 REF		
G		0.21 REF		
H	0.180	0.212	0.244	
J	0.472	0.517	0.562	



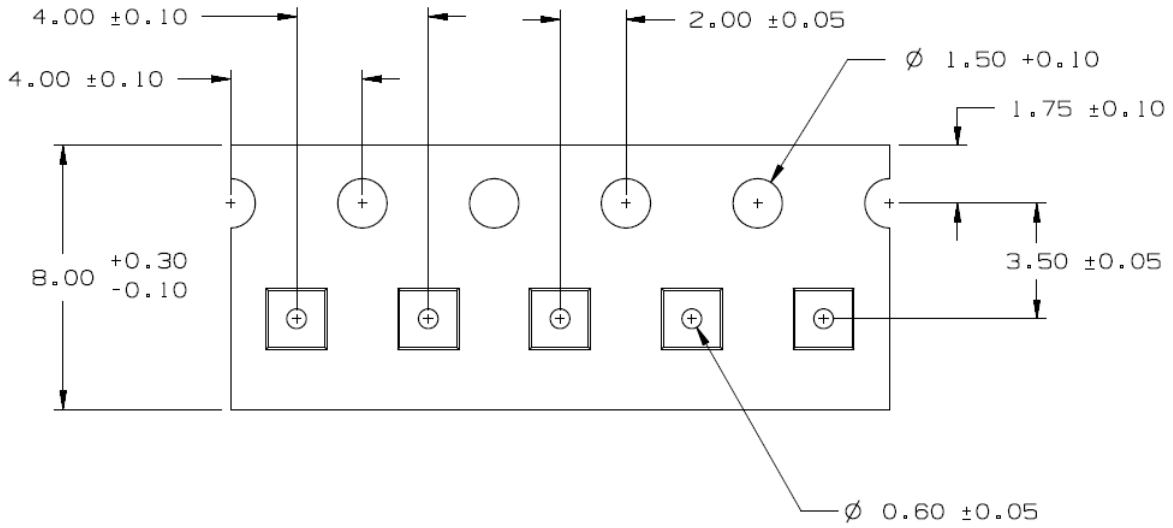
NOTE:

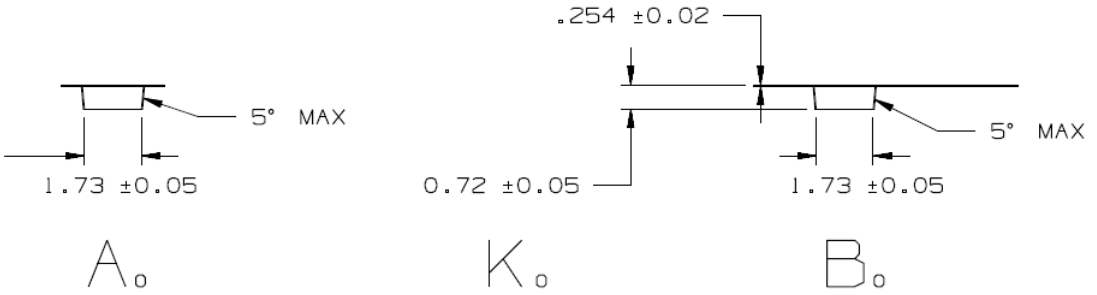
1)ALL DIMENSION ARE IN MILLIMETERS.
2)BOTTOM VIEW IS SOLDER BALL SIDE VIEW.
3)COMPLIES WITH JEDEC MO-211.
4)DRAWING IS NOT TO SCALE.
5)A,B IS PACKAGE SIZE



ROW	Description	Example
Row 1	Company Name	INN
Row 2	Product Code	XXX
Row 3	Lot Code	XXX
Row 4		XXX
Row 5	Date Code	YYWW
Row 6	Wafer ID	XX
Row 7	Location ID	XXXYYY

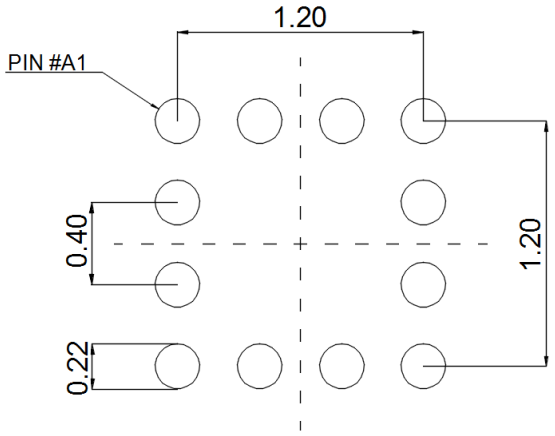
17. Tape and Reel Information





18. Recommended Land Pattern

WLCSP1.62X1.62-12L Package:



TOP VIEW

19. Order Information

Ordering Code	Package	Product Code	MSL	Packing (Tape & Reel)
INS2001W	WLCSP1.62x1.62-12L	2001W	MSL1	13” 2500PCS/reel

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